

## CMOS Quad 2-Input NAND Schmitt Triggers

High-Voltage Types (20 Volt Rating)

■ CD4093B consists of four Schmitt-trigger circuits. Each circuit functions as a two-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive- and negative-going signals. The difference between the positive voltage ( $V_p$ ) and the negative voltage ( $V_N$ ) is defined as hysteresis voltage ( $V_H$ ) (see Fig. 2).

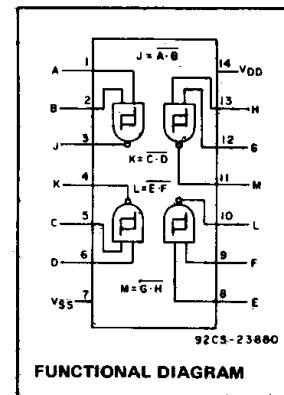
The CD4093B types are supplied in 14-lead hermetic dual-in-line ceramic packages (F3A suffix), 14-lead dual-in-line plastic packages (E suffix), 14-lead small-outline packages (M, MT, M96, and NSR suffixes), and 14-lead thin shrink small-outline packages (PW and PWR suffixes).

### Features:

- Schmitt-trigger action on each input with no external components
- Hysteresis voltage typically 0.9 V at  $V_{DD} = 5$  V and 2.3 V at  $V_{DD} = 10$  V
- Noise immunity greater than 50%
- No limit on input rise and fall times
- Standardized, symmetrical output characteristics
- 100% tested for quiescent current at 20 V
- Maximum input current of 1  $\mu$ A at 18 V over full package-temperature range, 100 nA at 18 V and 25°C
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

### Applications:

- Wave and pulse shapers
- High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators
- NAND logic



### RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges.

CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range ( $T_A = \text{Full Package Temp. Range}$ )	3	18	V

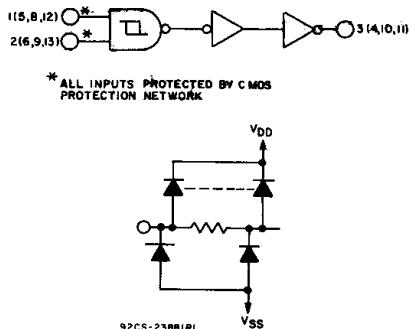


Fig. 1 – Logic diagram—1 of 4 Schmitt triggers.

### MAXIMUM RATINGS, Absolute-Maximum Values:

#### DC SUPPLY-VOLTAGE RANGE, ( $V_{DD}$ )

Voltages referenced to  $V_{SS}$  Terminal ..... -0.5V to +20V

INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to  $V_{DD}$  +0.5V

#### DC INPUT CURRENT (ANY ONE INPUT, $I_{IA}$ ) (See Note 1):

E package .....	$\pm 10\text{mA}$
M package .....	80°C/W
NS package .....	86°C/W

76°C/W

#### DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR  $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE}$  (All Package Types) ..... 100mW

OPERATING-TEMPERATURE RANGE ( $T_A$ ) ..... -55°C to +125°C

STORAGE TEMPERATURE RANGE ( $T_{stg}$ ) ..... -65°C to +150°C

#### LEAD TEMPERATURE (DURING SOLDERING):

At distance  $1/16 \pm 1/32$  inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

NOTE 1: Package thermal impedance is calculated in accordance with JESD 51-7.

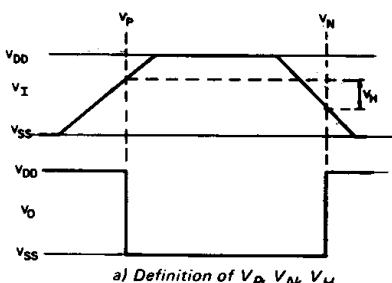
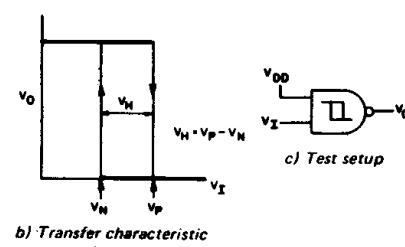


Fig. 2 – Hysteresis definition, characteristic, and test setup.



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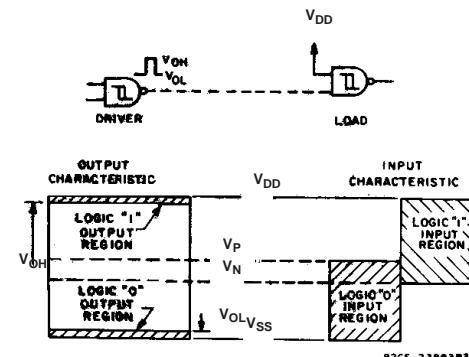


Fig. 3 – Input and output characteristics.

**STATIC ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)						UNITS	
	$V_O$ (V)	$V_{IN}$ (V)	$V_{DD}$ (V)	-55			+85				
				-55	-40	+85	+125	MIN.	TYP.		
Quiescent Device Current, $I_{DD}$ Max.	-	0.5	5	1	1	30	30	-	0.02	1	
	-	0.10	10	2	2	60	60	-	0.02	2	
	-	0.15	15	4	4	120	120	-	0.02	4	
	-	0.20	20	20	20	600	600	-	0.04	20	
Positive Trigger Threshold Voltage V <sub>P</sub> Min.	-	a	5	2.2	2.2	2.2	2.2	2.2	2.9	-	
	-	a	10	4.6	4.6	4.6	4.6	4.6	5.9	-	
	-	a	15	6.8	6.8	6.8	6.8	6.8	8.8	-	
	-	b	5	2.6	2.6	2.6	2.6	2.6	3.3	-	
	-	b	10	5.6	5.6	5.6	5.6	5.6	7	-	
	-	b	15	6.3	6.3	6.3	6.3	6.3	9.4	-	
	-	a	5	3.6	3.6	3.6	3.6	-	2.9	3.6	
	-	a	10	7.1	7.1	7.1	7.1	-	5.9	7.1	
	-	a	15	10.8	10.8	10.8	10.8	-	8.8	10.8	
	-	b	5	4	4	4	4	-	3.3	4	
	-	b	10	8.2	8.2	8.2	8.2	-	7	8.2	
	-	b	15	12.7	12.7	12.7	12.7	-	9.4	12.7	
Negative Trigger Threshold Voltage V <sub>N</sub> Min.	-	a	5	0.9	0.9	0.9	0.9	0.9	1.9	-	
	-	a	10	2.5	2.5	2.5	2.5	2.5	3.9	-	
	-	a	15	4	4	4	4	4	5.8	-	
	-	b	5	1.4	1.4	1.4	1.4	1.4	2.3	-	
	-	b	10	3.4	3.4	3.4	3.4	3.4	5.1	-	
	-	b	15	4.8	4.8	4.8	4.8	4.8	7.3	-	
	-	a	5	2.8	2.8	2.8	2.8	-	1.9	2.8	
	-	a	10	5.2	5.2	5.2	5.2	-	3.9	5.2	
	-	a	15	7.4	7.4	7.4	7.4	-	5.8	7.4	
	-	b	5	3.2	3.2	3.2	3.2	-	2.3	3.2	
	-	b	10	6.6	6.6	6.6	6.6	-	5.1	6.6	
	-	b	15	9.6	9.6	9.6	9.6	-	7.3	9.6	
Hysteresis Voltage V <sub>H</sub> Min.	-	a	5	0.3	0.3	0.3	0.3	0.3	0.9	-	
	-	a	10	1.2	1.2	1.2	1.2	1.2	2.3	-	
	-	a	15	1.6	1.6	1.6	1.6	1.6	3.5	-	
	-	b	5	0.3	0.3	0.3	0.3	0.3	0.9	-	
	-	b	10	1.2	1.2	1.2	1.2	1.2	2.3	-	
	-	b	15	1.6	1.6	1.6	1.6	1.6	3.5	-	
V <sub>H</sub> Max.	-	a	5	1.6	1.6	1.6	1.6	-	0.9	1.6	
	-	a	10	3.4	3.4	3.4	3.4	-	2.3	3.4	
	-	a	15	5	5	5	5	-	3.5	5	
	-	b	5	1.6	1.6	1.6	1.6	-	0.9	1.6	
	-	b	10	3.4	3.4	3.4	3.4	-	2.3	3.4	
	-	b	15	5	5	5	5	-	3.5	5	

\* Input on terminals 1,5,8,12 or 2,6,9,13; other inputs to  $V_{DD}$ .

\*\* Input on terminals 1 and 2, 5 and 6,8 and 9, or 12 and 13; other inputs to  $V_{DD}$ .

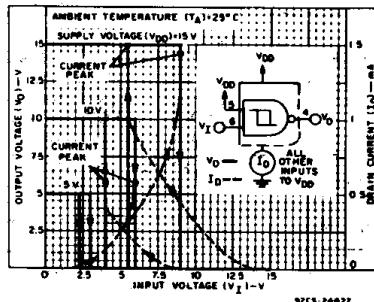


Fig. 4 – Typical current and voltage transfer characteristics.

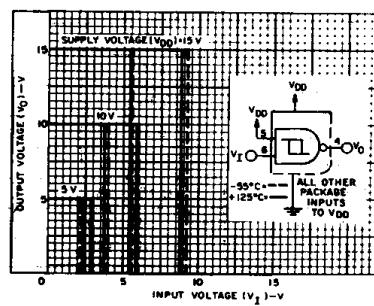


Fig. 5 – Typical voltage transfer characteristics as a function of temperature.

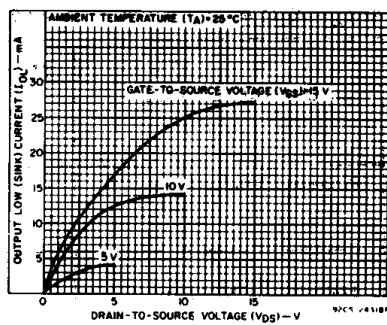


Fig. 6 – Typical output low (sink) current characteristics.

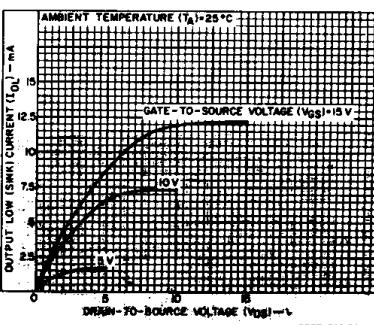


Fig. 7 – Minimum output low (sink) current characteristics.

## STATIC ELECTRICAL CHARACTERISTICS (CONT'D)

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)						UNITS		
	$V_O$ (V)	$V_{IN}$ (V)	$V_{DD}$ (V)	-55	-40	+85	+125	+25				
				MIN.	TYP.	MAX.	MIN.	TYP.	MAX.			
Output Low (Sink) Current, $I_{OL}$ Min.	0.4	0.5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA	
	0.5	0.10	10	1.6	1.5	1.1	0.9	1.3	2.6	—		
	1.5	0.15	15	4.2	4	2.8	2.4	3.4	6.8	—		
Output High (Source) Current, $I_{OH}$ Min.	4.6	0.5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA	
	2.5	0.5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—		
	9.5	0.10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—		
Output Voltage Low-Level, $V_{OL}$ Max.	—	0.5	5	0.05			—	0	0.05	V		
	—	0.10	10	0.05			—	0	0.05			
	—	0.15	15	0.05			—	0	0.05			
Output Voltage High-Level, $V_{OH}$ Min.	—	0.5	5	4.95			4.95	5	—	V		
	—	0.10	10	9.95			9.95	10	—			
	—	0.15	15	14.95			14.95	—	—			
Input Current, $I_{IN}$ Max.	—	0.18	18	$\pm 0.1$	$\pm 0.1$	$\pm 1$	$\pm 1$	—	$\pm 10^{-5}$	$\pm 0.1$	$\mu A$	

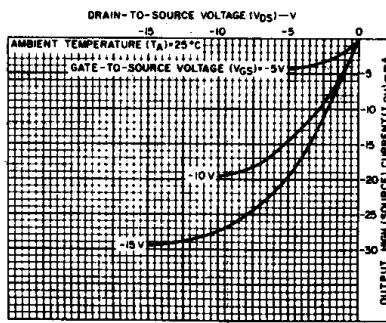


Fig. 8 – Typical output high (source) current characteristics.

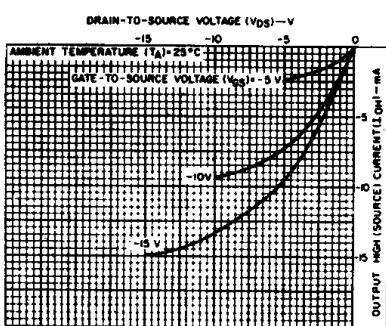


Fig. 9 – Minimum output high (source) current characteristics.

## DYNAMIC ELECTRICAL CHARACTERISTICS

At  $T_A = 25^\circ C$ ; Input  $t_r, t_f = 20\text{ ns}$ ,  $C_L = 50\text{ pF}$ ,  $R_L = 200\text{k}\Omega$

CHARACTERISTIC	TEST CONDITIONS		LIMITS		UNITS
	$V_{DD}$ VOLTS	TYP.	MAX.		
Propagation Delay Time: $t_{PHL}, t_{PLH}$		5 10 15	190	380	ns
			90	180	
			65	130	
Transition Time, $t_{THL}, t_{TLH}$		5 10 15	100	200	ns
			50	100	
			40	80	
Input Capacitance, $C_{IN}$	Any Input	5	7.5	pF	

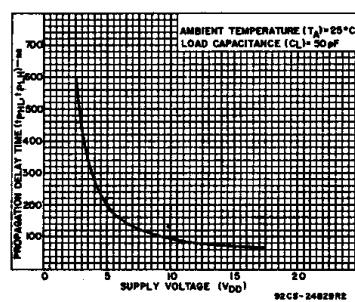


Fig. 10 – Typical propagation delay time vs. supply voltage.

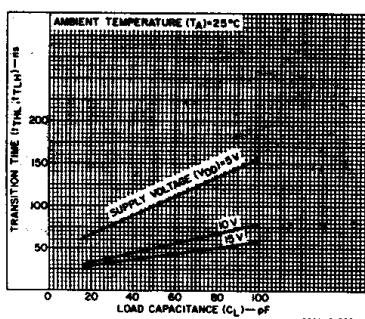


Fig. 11 – Typical transition time vs. load capacitance.

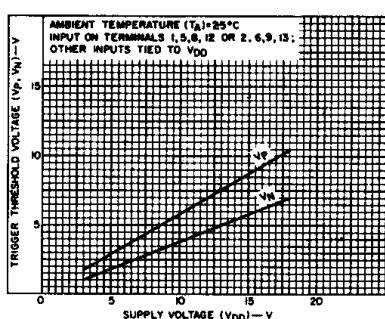


Fig. 12 – Typical trigger threshold voltage vs.  $V_{DD}$ .

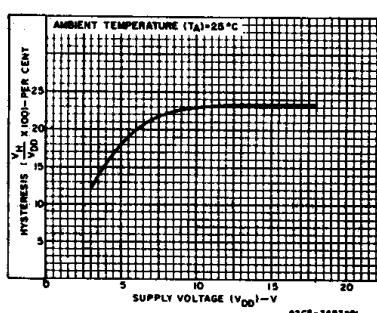


Fig. 13 – Typical per cent hysteresis vs. supply voltage.

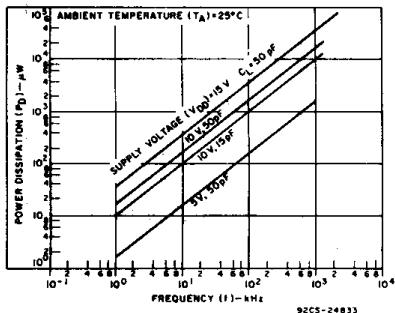


Fig. 14 – Typical power dissipation vs. frequency characteristics.

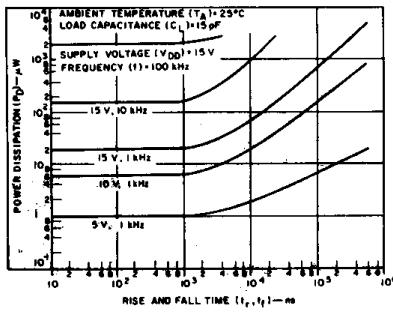


Fig. 15 – Typical power dissipation vs. rise and fall times.

## APPLICATIONS

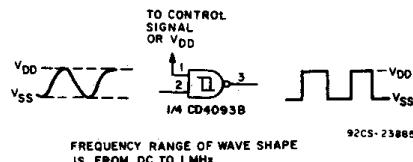


Fig. 16 – Wave shaper.

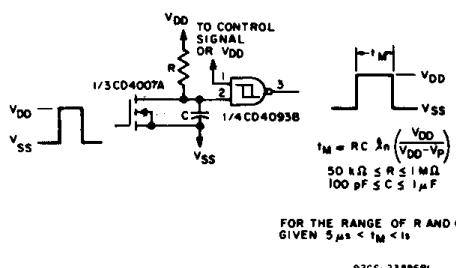


Fig. 17 – Monostable multivibrator.

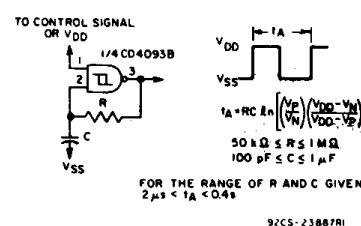


Fig. 18 – Astable multivibrator.

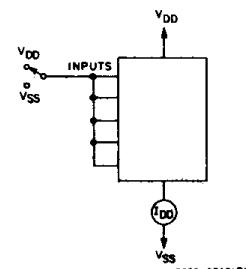


Fig. 19 – Quiescent device current test circuit.

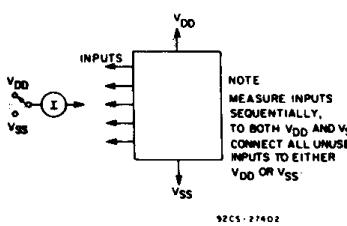
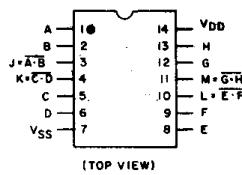


Fig. 20 – Input current test circuit.



TERMINAL ASSIGNMENT

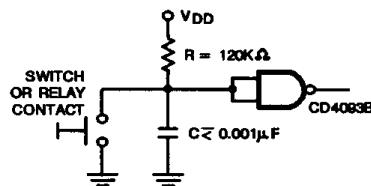


Fig. 21 – Contact Debouncer